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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/610,498 06/30/2003		Francis G. Celii	TI-34580	5368	
23494 75	590 03/14/2006		EXAMINER		
	RUMENTS INCOR	DEO, DUY VU NGUYEN			
P O BOX 6554 DALLAS, TX	,	ART UNIT	PAPER NUMBER		
·			1765		

DATE MAILED: 03/14/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application	on No.	Applicant(s)		
		10/610,49	10/610,498		CELII ET AL.	
Office Action Summary		Examiner	•	Art Unit		
		DuyVu n.	Deo	1765		
The MAII Period for Reply	LING DATE of this communicati	ion appears on the	e cover sheet wi	th the correspondence a	nddress	
WHICHEVER IS - Extensions of time I after SIX (6) MONT - If NO period for rep - Failure to reply with Any reply received	O STATUTORY PERIOD FOR B LONGER, FROM THE MAIL may be available under the provisions of 37 HS from the mailing date of this communication in the set or extended period for reply will, by the Office later than three months after the adjustment. See 37 CFR 1.704(b).	ING DATE OF TH CFR 1.136(a). In no evolation. y period will apply and will by statute, cause the app	HIS COMMUNIC ent, however, may a r ill expire SIX (6) MON lication to become AE	CATION. eply be timely filed THS from the mailing date of this HANDONED (35 U.S.C. § 133).		
Status						
2a) This actio	ve to communication(s) filed or n is FINAL . 2b)	This action is n	on-final.	ers, prosecution as to th	ne merits is	
closed in	accordance with the practice u	ınder <i>Ex parte Qu</i>	<i>ayl</i> e, 1935 C.D	. 11, 453 O.G. 213.		
Disposition of Clai	ims					
4a) Of the 5) ☐ Claim(s) _ 6) ☑ Claim(s) _ 7) ☐ Claim(s) _	3-7 and 9-13 is/are pending in above claim(s) is/are w is/are allowed. 3-7, 9-13 is/are rejected is/are objected to are subject to restriction	rithdrawn from co				
Application Papers	S					
	ication is objected to by the Ex	caminer.		•		
10) The drawi	ng(s) filed on is/are: a)[accepted or b)	objected to	by the Examiner.		
Applicant r	may not request that any objection	to the drawing(s) t	e held in abeyar	ce. See 37 CFR 1.85(a).		
	ent drawing sheet(s) including the	•	_	. , .	• •	
11) The oath o	or declaration is objected to by	the Examiner. No	ote the attached	I Office Action or form F	PTO-152.	
Priority under 35 L	J.S.C. § 119					
a) All b) [1. Cer 2. Cer 3. Cop app	dgment is made of a claim for f Some * c) None of: rtified copies of the priority doc rtified copies of the priority doc pies of the certified copies of the plication from the International ached detailed Office action for	uments have bee uments have bee ne priority docume Bureau (PCT Rul	n received. n received in A ents have been e 17.2(a)).	pplication No received in this Nationa	al Stage	
Attachment(s) 1) Notice of Reference	ces Cited (PTO-892)		4) Interview S	summary (PTO-413)		
2) Notice of Draftspe	rson's Patent Drawing Review (PTO-9 sure Statement(s) (PTO-1449 or PTO		Paper No(s	s)/Mail Date nformal Patent Application (P	TO-152)	

DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.
- 2. Claim 10 is rejected under 35 U.S.C. 102(e) as being anticipated by Ying et al. (US 2003/0176073).

Ying describes a method for forming a ferroelectric capacitor comprising: providing a dielectric oxide layer on the substrate 210 (paragraph [0016]); forming a barrier 220 over the dielectric layer (paragraph [0017]); providing a first metal Ir layer 230, a ferroelectric PZT layer 240 and a second Ir metal layer 250 in the order respectively (paragraphs [0018,0019]); forming a TiAlN hardmask over the Ir layer 250 (paragraph [0020]), etching the second Ir layer, the ferroelectric layer, and the first Ir layer using a plasma process at a T about 250-450 degrees C (paragraph [0028]). Wherein the sidewalls of the capacitor have an angle of greater than about 80 degrees (paragraph [0015]).

Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person

having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

4. Claims 3-7, 9, 11-13 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ying as applied to claim 10 above, and further in view of Moise et al. (US 6,211,035).

Ying describes etching the Ir layers using Cl2/O2/N2 and the PZT using Cl2/O2 (table 1). Unlike claimed invention, he doesn't describe the Ir etchant includes CO and the PZT etchant includes BCl3. Moise describes an etching method of Ir and PZT layers wherein he teaches the Cl2 and O2 sources can have BCl3 in addition to the Cl2 and CO in addition to O2 (col. 18, line 65-col. 19, line 13). It would have been obvious for one skilled in the art, in light of Moise, that BCl3 and CO can be added to the etchant of the Ir and PZT layers as a source of Cl2 and O2 to etch the Ir and the PZT layers with a reasonable expectation of success.

Referring to claims 3, 6, and 12, applied prior art of Moise doesn't describe the gases ratios of BCl3 and Cl2 are from 1:4-10:1. However, one skilled in the art would find it obvious to determine the gases ratios from the routine experimentation in order to provide optimum ratios of etching gases including BCl3 and Cl2 to etch the PZT layer with a reasonable expectation of success.

Response to Arguments

5. Applicant's arguments filed 1/10/06 have been fully considered but they are not persuasive.

Applicant's argument that the cited ratio range of the present is not recognized by the cited art as a result-effective variable because they don't indicate that a ratio range may impact the sidewall profile of the capacitor stack is found unpersuasive because it is not necessary to show that a ratio range may impact the sidewall profile of the capacitor stack in order to

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recognize that the ratio range is a result-effective variable. It would be within one skilled in the art to recognize that any processing parameter is a result-effective variable, especially the concentration of an etchant. It would be obvious to one skilled in the art that changing the concentration of the etchant would certainly change the etch rate. Therefore, one skilled in the art at the time of the invention would find it obvious to determine the ratio or concentration of the etchant through test runs in order to provide an optimum range to etch the PZT.

Referring to applicant's argument that Ying does not teach forming sidewalls having angle between 78 and 88 degree. Please see paragraph [0015] where he teaches the sidewalls angle is about 80 degree, which would certain an angle between 78 and 88 degree.

Conclusion

6. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to DuyVu n. Deo whose telephone number is 571-272-1462.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571-272-1465. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Primary Examiner Duy-Vu N. Deo 3/9/06